

# IRG4PSC71UPbF

INSULATED GATE BIPOLAR TRANSISTOR

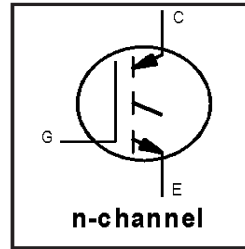
UltraFast Speed IGBT

## Features

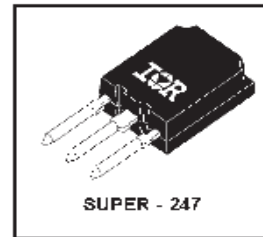
- UltraFast switching speed optimized for operating frequencies 8 to 40kHz in hard switching, 200kHz in resonant mode soft switching
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency (minimum switching and conduction losses) than prior generations
- Industry-benchmark Super-247 package with higher power handling capability compared to same footprint TO-247
- Creepage distance increased to 5.35mm
- Lead-Free

## Benefits

- Generation 4 IGBT's offer highest efficiencies available
- Maximum power density, twice the power handling of the TO-247, less space than TO-264
- IGBTs optimized for specific application conditions
- Cost and space saving in designs that require multiple, paralleled IGBTs



|                                   |
|-----------------------------------|
| $V_{CES} = 600V$                  |
| $V_{CE(on)} \text{ typ.} = 1.67V$ |
| @ $V_{GE} = 15V, I_C = 60A$       |



## Absolute Maximum Ratings

|                                         | Parameter                              | Max.                              | Units |
|-----------------------------------------|----------------------------------------|-----------------------------------|-------|
| V <sub>CES</sub>                        | Collector-to-Emitter Breakdown Voltage | 600                               | V     |
| I <sub>C</sub> @ T <sub>C</sub> = 25°C  | Continuous Collector Current           | 85⑥                               | A     |
| I <sub>C</sub> @ T <sub>C</sub> = 100°C | Continuous Collector Current           | 60                                |       |
| I <sub>CM</sub>                         | Pulsed Collector Current ①             | 200                               |       |
| I <sub>LM</sub>                         | Clamped Inductive Load Current ②       | 200                               |       |
| V <sub>GE</sub>                         | Gate-to-Emitter Voltage                | ± 20                              | V     |
| E <sub>ARV</sub>                        | Reverse Voltage Avalanche Energy ③     | 180                               | mJ    |
| P <sub>D</sub> @ T <sub>C</sub> = 25°C  | Maximum Power Dissipation              | 350                               | W     |
| P <sub>D</sub> @ T <sub>C</sub> = 100°C | Maximum Power Dissipation              | 140                               |       |
| T <sub>J</sub>                          | Operating Junction and                 | -55 to + 150                      | °C    |
| T <sub>STG</sub>                        | Storage Temperature Range              |                                   |       |
|                                         | Soldering Temperature, for 10 seconds  |                                   |       |
|                                         |                                        | 300 (0.063 in. (1.6mm from case ) |       |

## Thermal Resistance\ Mechanical

|                 | Parameter                                 | Min.      | Typ.     | Max. | Units        |
|-----------------|-------------------------------------------|-----------|----------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case                          | —         | —        | 0.36 | $^\circ C/W$ |
| $R_{\theta CS}$ | Case-to-Sink, flat, greased surface       | —         | 0.24     | —    |              |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | —         | —        | 38   |              |
|                 | Recommended Clip Force                    | 20.0(2.0) | —        | —    | N (kgf)      |
|                 | Weight                                    | —         | 6 (0.21) | —    | g (oz)       |

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

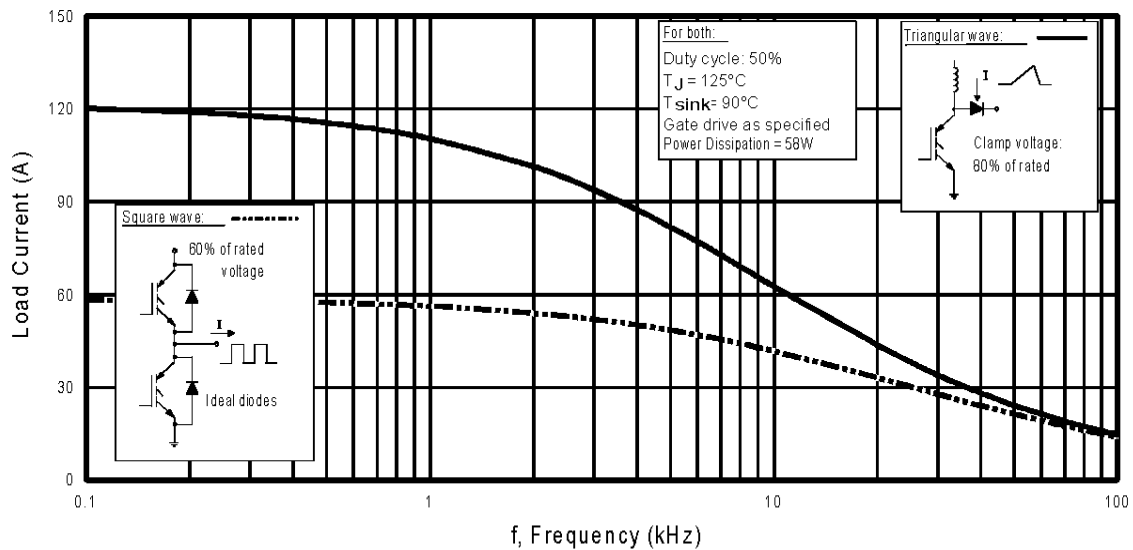
|                                 | Parameter                                | Min. | Typ. | Max.      | Units   | Conditions                                            |
|---------------------------------|------------------------------------------|------|------|-----------|---------|-------------------------------------------------------|
| $V_{(BR)CES}$                   | Collector-to-Emitter Breakdown Voltage   | 600  | —    | —         | V       | $V_{GE} = 0V, I_C = 250\mu A$                         |
| $V_{(BR)ECS}$                   | Emitter-to-Collector Breakdown Voltage ④ | 18   | —    | —         | V       | $V_{GE} = 0V, I_C = 1.0A$                             |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage  | —    | 0.45 | —         | V/°C    | $V_{GE} = 0V, I_C = 5.0mA$                            |
| $V_{CE(ON)}$                    | Collector-to-Emitter Saturation Voltage  | —    | 1.67 | 2.0       | V       | $I_C = 60A, V_{GE} = 15V$                             |
|                                 |                                          | —    | 1.95 | —         |         | $I_C = 100A, V_{GE} = 15V$                            |
|                                 |                                          | —    | 1.71 | —         |         | $I_C = 60A, T_J = 150^\circ\text{C}$                  |
| $V_{GE(th)}$                    | Gate Threshold Voltage                   | 3.0  | —    | 6.0       |         | $V_{CE} = V_{GE}, I_C = 250\mu A$                     |
| $\Delta V_{GE(th)}/\Delta T_J$  | Temperature Coeff. of Threshold Voltage  | —    | -10  | —         | mV/°C   | $V_{CE} = V_{GE}, I_C = 1.0mA$                        |
| $g_{fe}$                        | Forward Transconductance ⑤               | 47   | 70   | —         | S       | $V_{CE} = 50V, I_C = 60A$                             |
| $I_{CES}$                       | Zero Gate Voltage Collector Current      | —    | —    | 500       | $\mu A$ | $V_{GE} = 0V, V_{CE} = 600V$                          |
|                                 |                                          | —    | —    | 2.0       |         | $V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$   |
|                                 |                                          | —    | —    | 5.0       | mA      | $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$ |
| $I_{GES}$                       | Gate-to-Emitter Leakage Current          | —    | —    | $\pm 100$ | nA      | $V_{GE} = \pm 20V$                                    |

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

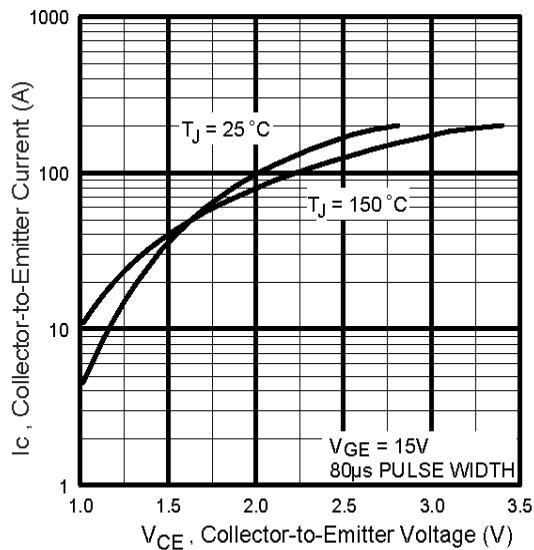
|              | Parameter                         | Min. | Typ. | Max. | Units | Conditions                      |
|--------------|-----------------------------------|------|------|------|-------|---------------------------------|
| $Q_g$        | Total Gate Charge (turn-on)       | —    | 340  | 520  | nC    | $I_C = 60A$                     |
| $Q_{ge}$     | Gate - Emitter Charge (turn-on)   | —    | 44   | 66   |       | $V_{CC} = 400V$                 |
| $Q_{gc}$     | Gate - Collector Charge (turn-on) | —    | 160  | 240  |       | $V_{GE} = 15V$                  |
| $t_{d(on)}$  | Turn-On Delay Time                | —    | 34   | —    | ns    | $T_J = 25^\circ\text{C}$        |
| $t_r$        | Rise Time                         | —    | 50   | —    |       | $I_C = 60A, V_{CC} = 480V$      |
| $t_{d(off)}$ | Turn-Off Delay Time               | —    | 56   | 84   |       | $V_{GE} = 15V, R_G = 5.0\Omega$ |
| $t_f$        | Fall Time                         | —    | 86   | 130  | mJ    | Energy losses include "tail"    |
| $E_{on}$     | Turn-On Switching Loss            | —    | 0.42 | —    |       | See Fig. 10, 11, 13, 14         |
| $E_{off}$    | Turn-Off Switching Loss           | —    | 1.99 | —    |       |                                 |
| $E_{ts}$     | Total Switching Loss              | —    | 2.41 | 3.2  | ns    | $T_J = 150^\circ\text{C}$       |
| $t_{d(on)}$  | Turn-On Delay Time                | —    | 30   | —    |       | $I_C = 60A, V_{CC} = 480V$      |
| $t_r$        | Rise Time                         | —    | 49   | —    |       | $V_{GE} = 15V, R_G = 5.0\Omega$ |
| $t_{d(off)}$ | Turn-Off Delay Time               | —    | 129  | —    | mJ    | Energy losses include "tail"    |
| $t_f$        | Fall Time                         | —    | 175  | —    |       | See Fig. 13, 14                 |
| $E_{ts}$     | Total Switching Loss              | —    | 4.5  | —    |       |                                 |
| $L_E$        | Internal Emitter Inductance       | —    | 13   | —    | nH    | Measured 5mm from package       |
| $C_{ies}$    | Input Capacitance                 | —    | 7500 | —    | pF    | $V_{GE} = 0V$                   |
| $C_{oes}$    | Output Capacitance                | —    | 720  | —    |       | $V_{CC} = 30V$                  |
| $C_{res}$    | Reverse Transfer Capacitance      | —    | 93   | —    |       | $f = 1.0MHz$                    |

### Notes:

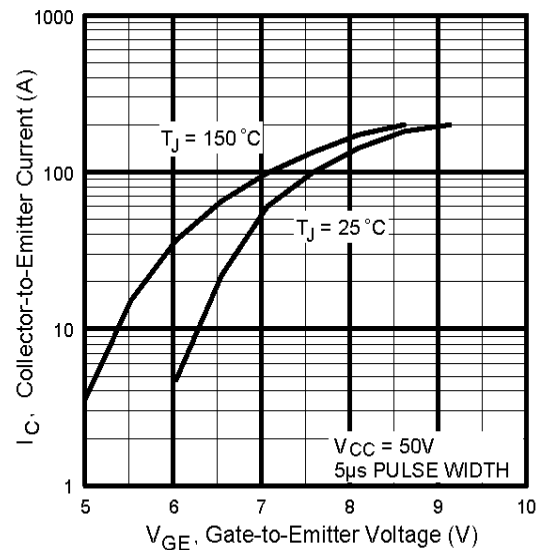
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES})$ ,  $V_{GE} = 20V$ ,  $L = 10\mu H$ ,  $R_G = 5.0\Omega$ , (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.
- ⑥ Current limited by the package, (Die current = 100A)



**Fig. 1** - Typical Load Current vs. Frequency  
(For square wave,  $I = I_{\text{RMS}}$  of fundamental; for triangular wave,  $I = I_{\text{PK}}$ )



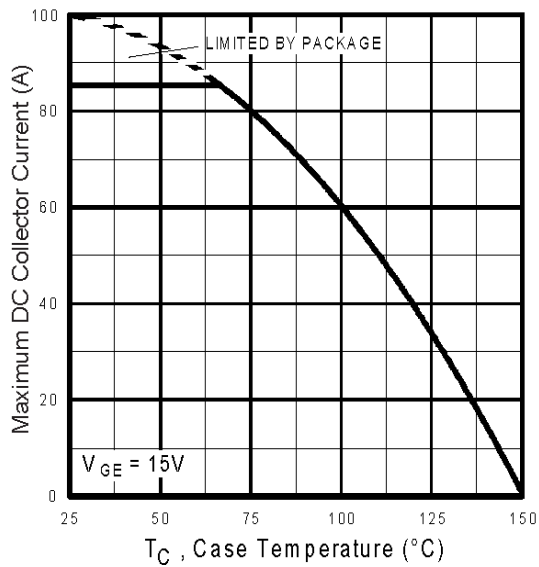
**Fig. 2** - Typical Output Characteristics



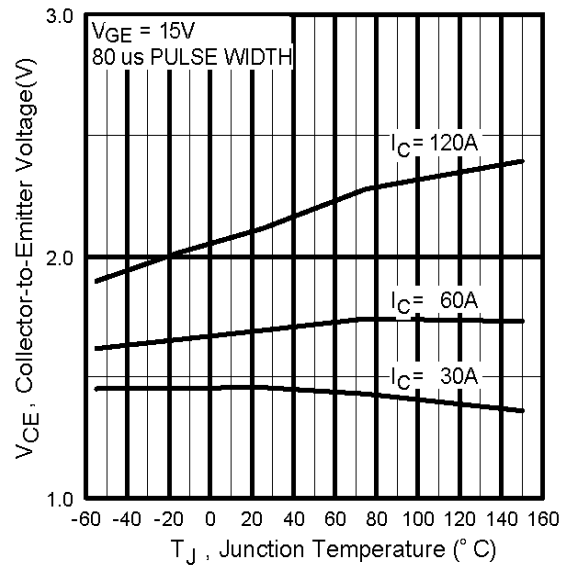
**Fig. 3** - Typical Transfer Characteristics

# IRG4PSC71UPbF

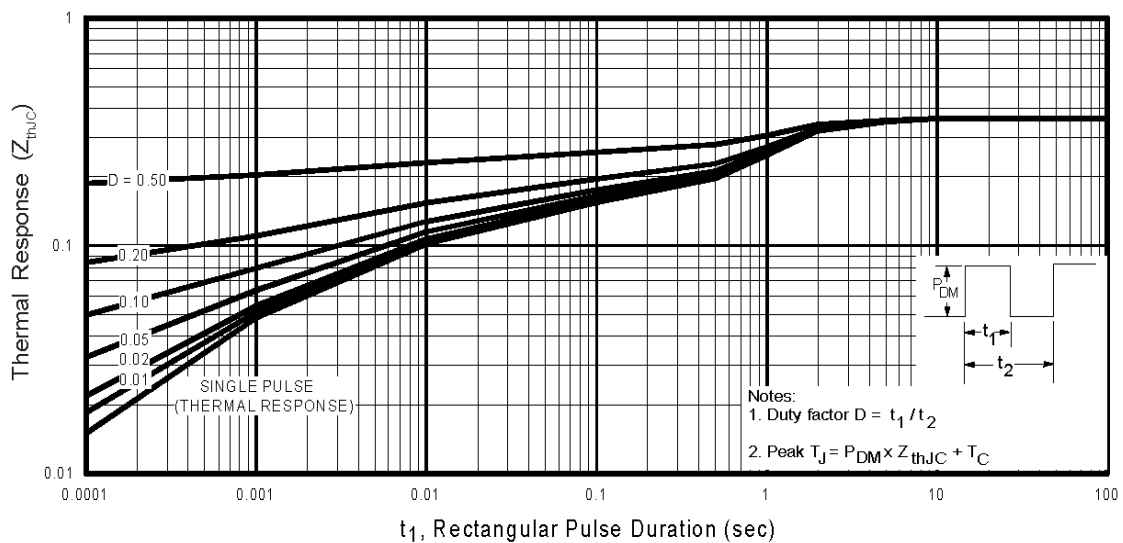
International  
**IR** Rectifier



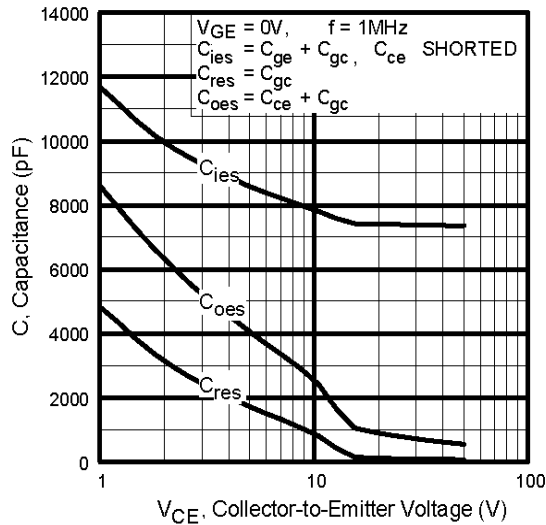
**Fig. 4** - Maximum Collector Current vs. Case Temperature



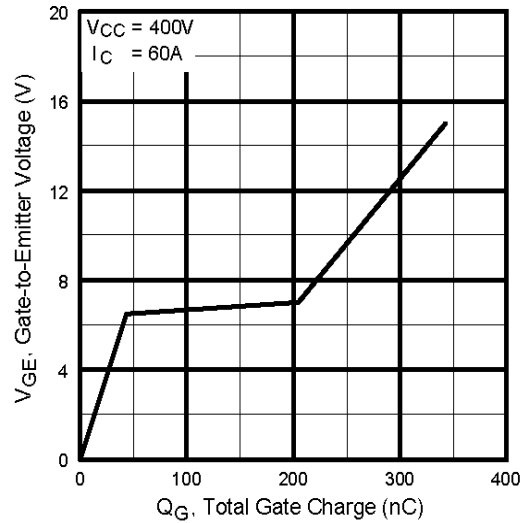
**Fig. 5** - Collector-to-Emitter Voltage vs. Junction Temperature



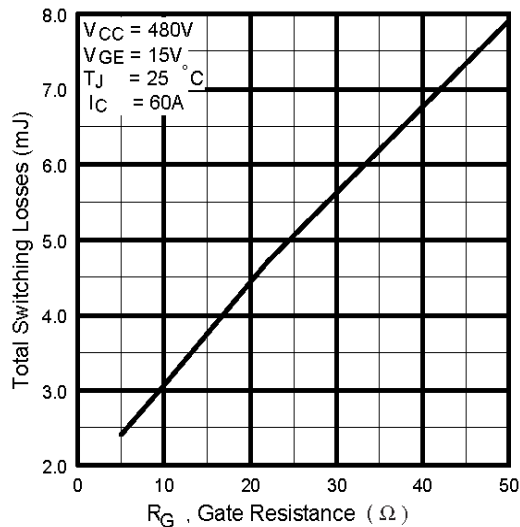
**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case



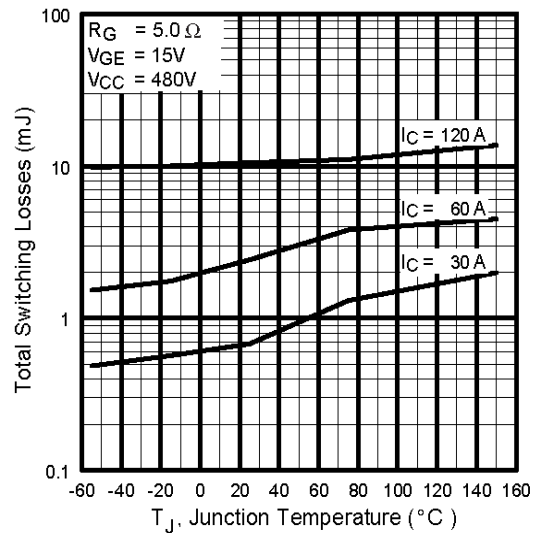
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



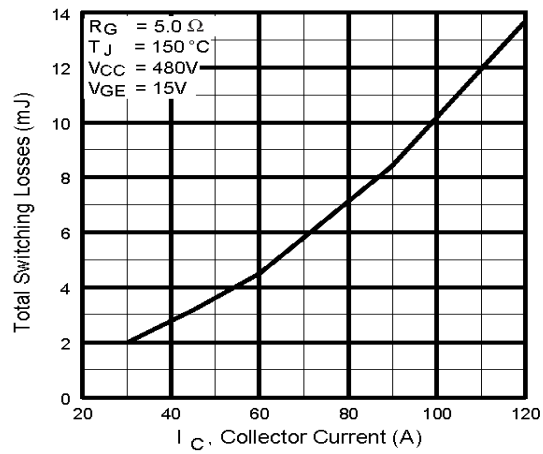
**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



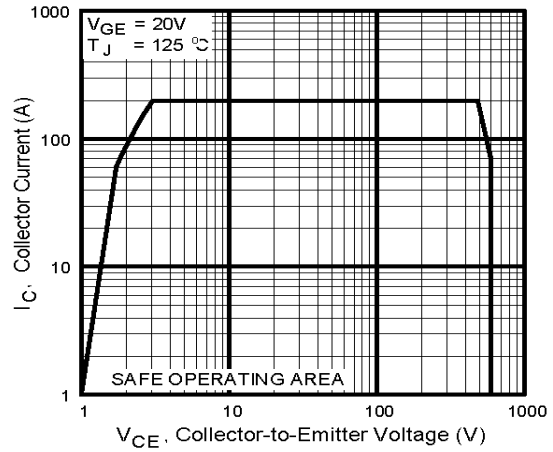
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



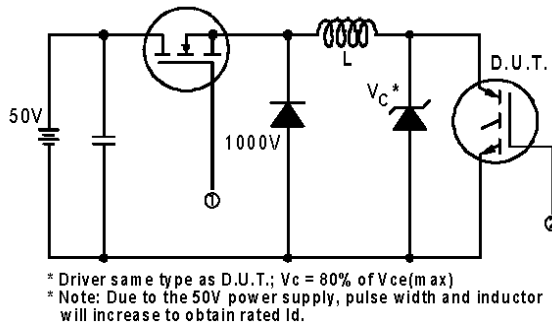
**Fig. 10** - Typical Switching Losses vs. Junction Temperature



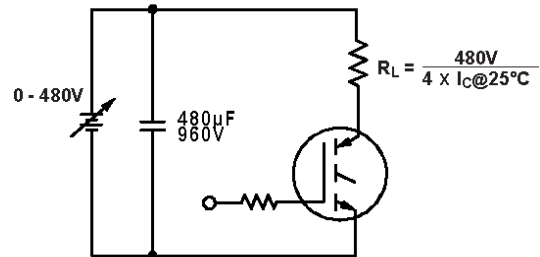
**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



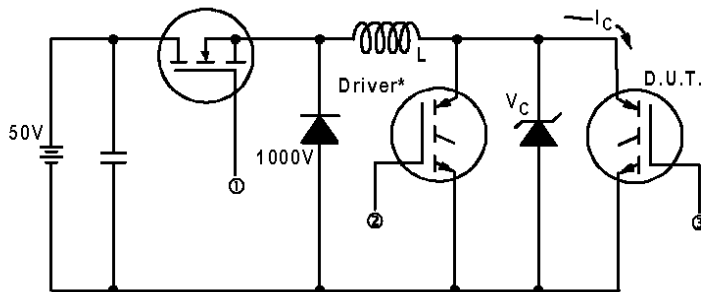
**Fig. 12** - Turn-Off SOA



**Fig. 13a** - Clamped Inductive Load Test Circuit

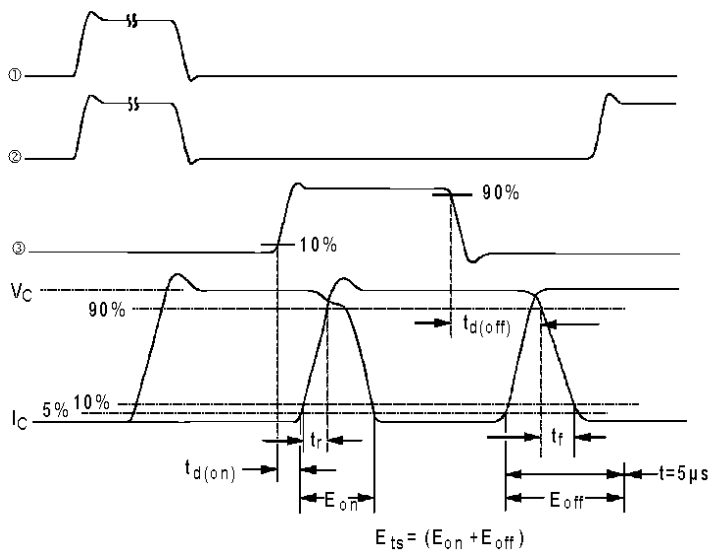


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T.,  $V_c = 480V$

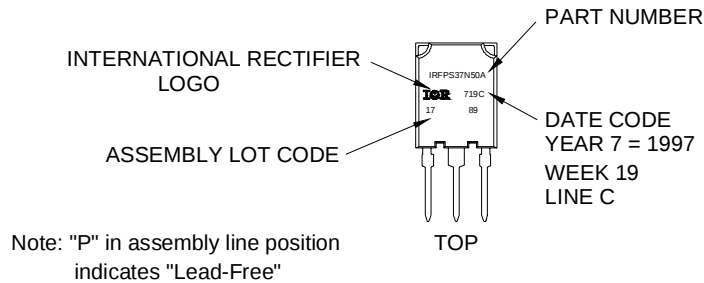


**Fig. 14b** - Switching Loss Waveforms

## Case Outline and Dimensions — Super-247

[illegible]

EXAMPLE: THIS IS AN IRFPS37N50A WITH  
ASSEMBLY LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"



Data and specifications subject to change without notice.

International  
**IOR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

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